

GAE

GREAT AMERICAN ELECTROINCS

2N6369

Silicon NPN power VHF transistor 2N6369 is designed for wideband large-signal output amplifier stages of transmitter communications apparatus.

Output Power: 80 Watt
Frequency Range: 50-200 Mhz
Voltage: 28 V
Package Type: SOT-119
Common Emitter Configuration
NiChrome Emitter Resistors
Aluminum Metalization
Internal Input Matching
Optimum Load Mismatch Capability

Electrical Characteristics ($T_{CASE}=40^{\circ}C$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{out}	$f_o = 175 \text{ Mhz}/V_{cc}=28V/P_{IN}=20W$	80			W
G_p	$f_o = 400 \text{ Mhz}/V_{cc}=28V/P_{out}=80W$	6			dB
λ_c	$f_o = 400 \text{ Mhz}/V_{cc}=28V/P_{out}=80W$	50	60		%

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

SYMBOL	PARAMETERS	VALUE	UNIT
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	4	V
I_c	Continuous Collector Current	15	A
P_C	Collector Power Dissipation	150*	W
T_j	Junction Temperature	160	$^{\circ}C$
$R_{th(j-c)}$	Junction-Case Thermal Resistance	0.8	$^{\circ}C/W$

*For Dynamic Operation, $T_{CASE} = 40^{\circ}C$